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PTO/SB/08A (10-96)
Appr. for use through 10/31/99. OMB 0651-0031

App. for use through 1984. GPO 1981-839
Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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<p>Substitute for form 1449A/PTO (Modified by BSTZ 6/30/99)</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p><i>(use as many sheets as necessary)</i></p>				<p><i>Complete if Known</i></p>	
				<p>Application Number</p>	<p>New Application</p>
				<p>Filing Date</p>	<p>Herewith</p>
				<p>First Named Inventor</p>	<p>Jack Zezhong Peng</p>
				<p>Group Art Unit</p>	<p>Not yet assigned</p>
				<p>Examiner Name</p>	<p>Not yet assigned</p>
Sheet	1	of	1	Attorney Docket Number	005819.P001
					

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS

OTHER DOCUMENTS		
Examiner Initials *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published (if known).	Translation? Yes/No
HN	MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO ₂ Films; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
HN	LOMBARDO, S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFET's at Low Inversion Layer Density; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
HN	WU, E.W. et al; Voltage-Dependent Voltage-Acceleration of Oxide Breakdown for Ultra-Thin Oxides; IEEE, 2000.	
HN	RASRAS, MAHMOUD et al; Substrate Hole Current Origin After Oxide Breakdown; IEEE, 2000.	
HN	SUNE, JORDI et al.; Post Soft Breakdown Conduction in SiO ₂ Gate Oxides; IEEE, 2000.	

Examiner
Signature

HIEN NGUYEN

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Considered

4/29/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT Form PTO-1449 (Modified) (Use several sheets if necessary)				COMPLETED IF KNOWN	
				Application Number	09/955,641
				Confirmation Number	1777
				Filing Date	09/18/2001
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	2818
				Examiner Name	
Sheet		1	of	1	Attorney Docket No.
				384848001US	

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document
		NUMBER	Kind Code (if known)		
HJ		4,490,900		Chiu	01/01/85
HJ		5,578,848		Kwong et al.	11/26/96
HJ		6,034,893		Mehta	03/07/00
HJ		6,064,595		Logie et al.	05/16/00
HJ		6,157,568		Schmidt	12/05/00
HJ		6,214,666		Mehta	04/10/01
HJ		6,215,140		Reisinger et al.	04/10/01
HJ		6,232,631		Schmidt et al.	05/15/01
HJ		6,282,123		Mehta	08/28/01
HJ		6,294,809		Logie	09/25/01
HJ		6,297,103		Ahn et al.	10/02/01
FOREIGN PATENT DOCUMENTS					
Examiner Initial	Cite No.	Foreign Patent or Application		Name of Patentee or Applicant of Cited Document	Date of Publication or Filing Date of Cited Document
		Office	NUMBER		
OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume issue number(s), publisher, city and/or country where published.			

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT OCT 15 2002 Form PTO-1449 (Modified) Use several sheets if necessary			COMPLETE IF KNOWN	
			Application Number	09/955,641
			Confirmation Number	1777
			Filing Date	09/18/2001
			First Named Inventor	Jack Zezhong Peng
			Group Art Unit	2818 2824
			Examiner Name	
1	of	1	Attorney Docket No.	384848001US

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EXAMINER	HIEU NGUYEN	DATE CONSIDERED	4/29/04
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NOV 18 2002 Form PTO-1449 (Modified) (Use several sheets if necessary)				Application Number	09/955,641
				Confirmation Number	1777
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				Group Art Unit	2818
				Examiner Name	
Sheet	1	of	1	Attorney Docket No.	384848001US

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Examiner Initial	Cite No.	Foreign Patent or Application		Name of Patentee or Applicant of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear
		Office	NUMBER			

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Electronic Information Disclosure Statement

SEMICONDUCTOR MEMORY CELL AND MEMORY ARRAY USING A BREAKDOWN PHENOMENA IN AN ULTRA-THIN DIELECTRIC

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Application: 09/955641

Confirmation: 1777

Applicant(s): Jack Peng

Docket Number: 384848001US

Group Art Unit: 2818

Examiner:

search string: (3634929 or 4322822 or 4488262 or 4502208 or 4507757 or 4543594 or 4613886 or 4823181 or 4876220 or 4899205 or 4943538 or 5138410 or 5304871 or 5412244 or 5496756 or 5576568 or 5587603 or 5600265 or 5675541 or 5825200 or 5825201 or 5880512 or 5909049 or 6084428 or 6097077 or 6421293).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
h	P01	3634929	1972-01-18		Yoshida et al.	29	577
h	P02	4322822	1982-03-30		McPherson	365	182
h	P03	4488262	1984-12-11		Basire et al.	365	104
h	P04	4502208	1985-03-05		McPherson	438	281
h	P05	4507757	1985-03-26		McElroy	365	104

HN	P06	4543594	1985-09-24		Mohsen et al.	257	530
↑	P07	4613886	1986-09-23		Chwang	257	369
	P08	4823181	1989-04-18		Mohsen et al.	257	530
	P09	4876220	1989-10-24		Mohsen et al.	438	200
	P10	4899205	1990-02-06		Hamdy et al.	257	530
	P11	4943538	1990-07-24		Mohsen et al.	438	215
	P12	5138410	1992-08-11		Takebuchi	257	314
	P13	5304871	1994-04-19		Dharmarajan et al.	326	44
	P14	5412244	1995-05-02		Hamdy et al.	257	530
	P15	5496756	1996-03-05		Sharma et al.	438	258
	P16	5576568	1996-11-19		Kowshik	257	318
	P17	5587603	1996-12-24		Kowshik	257	316
	P18	5600265	1997-02-04		El Gamal et al.	326	41
	P19	5675541	1997-10-07		Leterrier	365	189.01
	P20	5825200	1998-10-20		Kolze	326	38
	P21	5825201	1998-10-20		Kolze	326	39
	P22	5880512	1999-03-09		Gordon et al.	257	530
	P23	5909049	1999-06-01		McCollum	257	530
	P24	6084428	2000-07-04		Kolze et al.	326	41
✓	P25	6097077	2000-08-01		Gordon et al.	257	530
HN	P26	6421293	2002-07-16		Candelier et al.	365	225.7

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Examiner Name	Date
H. NGUEN	4/29/04

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13.03.2003

Electronic Information Disclosure Statement

SEMICONDUCTOR MEMORY CELL AND MEMORY ARRAY USING A BREAKDOWN PHENOMENA IN AN ULTRA-THIN DIELECTRIC

Application:



09/955641

Confirmation:

1777

Applicant(s):

Jack Peng

Docket Number:

384848001.US

Group Art Unit:

2824

Examiner:

Hien N. Nguyen

search string:

(4677742 or 4599705).pn.

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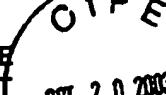
US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
HN	PO1	4677742	1987-07-07		Johnson	29	591
HN	PO2	4599705	1986-07-08		Holmberg et al.	365	163

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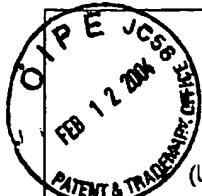
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H. NGUYEN	4/29/04

INFORMATION DISCLOSURE STATEMENT BY APPLICANT Form PTO-1449 (Modified) (Use several sheets if necessary)				COMPLETE IF KNOWN	
				Application Number 09/955,641 Confirmation Number 1777 Filing Date 09/18/2001 First Named Inventor Jack Zezhong Peng Group Art Unit 2818 Examiner Name	
Sheet	1	of	1	Attorney Docket No. 384848001US	

FOREIGN PATENT DOCUMENTS						
Examiner Initial	Cite No.	Foreign Patent or Application		Name of Patentee or Applicant of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear
		Office	NUMBER			
HN		EP	0 295 935	A1	Advanced Micro Devices, Inc.	12/21/88
HN		JP	61292295	Fujitsu Ltd.	12/23/86	

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume issue number(s), publisher, city and/or country where published.		

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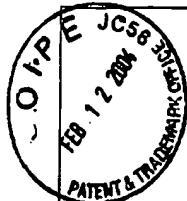
Sheet 1 of 2

COMPLETE IF KNOWN

Application Number 09/955,641
Confirmation Number 1777
Filing Date 09/18/2001
First Named Inventor Jack Zenghong Fan
Group Art Unit 2815
Examiner Name
Attorney Docket No. 384848001US

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear
		NUMBER	Kind Code (if known)			
HN		4,546,273		Osman	10/08/85	
		4,758,986		Kuo	07/19/88	
		4,794,562		Kato et al.	12/27/88	
		4,962,342		Mead et al.	10/09/90	
		5,150,179		Gill	09/22/92	
		5,303,185		Hazani	04/12/94	
		5,323,342		Wada et al.	06/21/94	
		5,477,499		Van Buskirk et al.	12/19/95	
		5,586,270		Rotier et al.	12/17/96	
		5,745,417		Kobayashi et al.	04/28/98	
		5,986,931		Caywood	11/16/99	
		5,986,939		Yamada	11/16/99	
		6,016,268		Worley	01/18/00	
		6,040,968		Duvvury et al.	03/21/00	
		6,166,954		Chern	12/26/00	
		6,218,274		Komatsu	04/17/01	
		6,249,809		Bro	06/19/01	
		6,304,666		Warren et al.	10/16/01	
		6,351,428		Forbes	02/26/02	
		6,431,456		Nishizawa et al.	08/13/02	
		6,456,535		Forbes et al.	09/24/02	
HN		6,556,481		Hsu et al.	04/29/03	
HN		US2001/0003374		Bohmer et al.	06/14/01	

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STATEMENT BY APPLICANT
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Application Number 09/955,641
Confirmation Number 1777
Filing Date 09/18/2001
First Named Inventor Jack Zezhong Peng
Group Art Unit 2818
Examiner Name

Attorney Docket No. 38484800106

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U.S. Patent or Application				

FOREIGN PATENT DOCUMENTS

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HN		DeGRAAF, C., et al, A Novel High-Density Low-Cost Diode Programmable Read Only Memory, IEEE, 1996.	

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